Features

Freq: 2～8GHz

Slope: 2 dB

Insertion Loss: 0.5dB@8GHz

Chip Size: 0.88mm×0.8mm×0.1mm

General Description

The HG115J is a GaAs pHEMT equalizer. Covering 2 to 8 GHz, this equalizer offers very high slope of 2 dB and extremely low insertion loss of 0.5dB@8GHz. Input and output VSWR are 1.1/1.1.

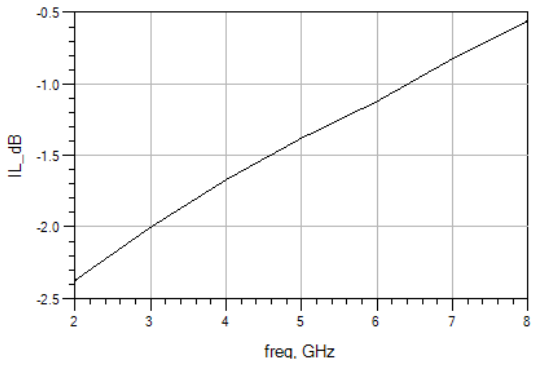
Electrical Specifications(T_A=25 ℃)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)		2～8	
Input VSWR	-	1.1	-
Output VSWR	-	1.1	-
Insertion Loss(dB)	-	0.5~2.5	-
Slope(dB)	-	2	-

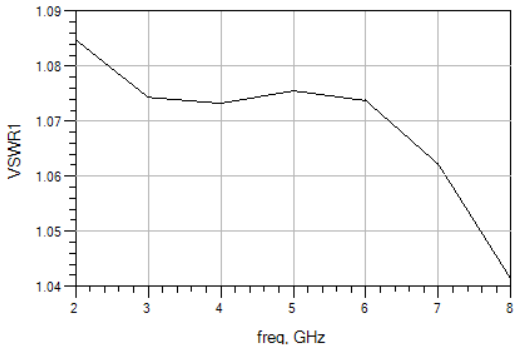
Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55℃～125℃
Storage Temperature	-65℃～150℃

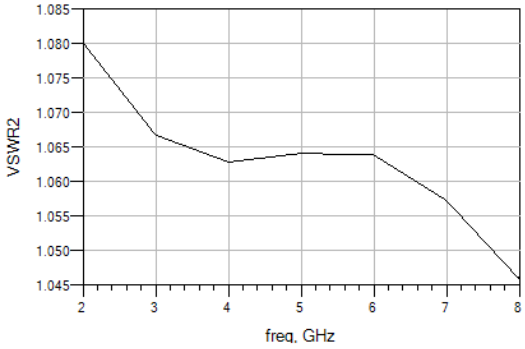
Insertion Loss



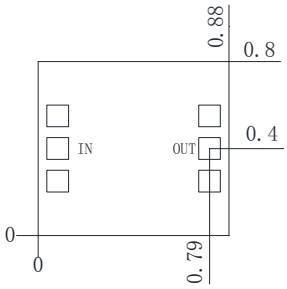
Input VSWR



Output VSWR



Outline Drawing (mm)



Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300℃, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with Φ25μm double gold wire bonding, suggested length of gold wire 250～400μm.
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.